



N-Channel 80 V (D-S) Super Junction Power MOSFET

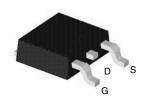
PRODUCT SUMMARY						
V _{(BR)DSS} (V)	$r_{DS(on)}$ (Ω)	I _D (A) ^c	Q _g (Typ.)			
80	0.0039 at V _{GS} = 10 V	120	83 nC			
	0.0062 at V _{GS} = 4.5 V	70	03110			

FEATURES

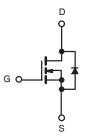




TO-252 Pin Configuration



Top View



• 100 % $\rm R_{\rm g}$ and UIS Tested

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Gate-Source Voltage		V _{GS}	± 20	V		
Continuous Drain Current (T _{.I} = 175 °C) ^b	T _C = 25 °C	ID	120			
Continuous Drain Current (1 _J = 175 °C) ²	T _C = 100 °C	l 'b	70 ^a			
Pulsed Drain Current	I _{DM}	480	А			
Continuous Source Current (Diode Conduction)	I _S	120				
Avalanche Current		I _{AS}	115			
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AS}	258	mJ		
Maximum Dawar Dissination	T _C = 25 °C	P _D	351	W		
Maximum Power Dissipation	T _C = 125 °C	'D	117			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	t ≤ 10 sec	R _{thJA}	12	20	°C/W	
Waximum Junction-to-Ambient	Steady State	' 'thJA	21	35		
Maximum Junction-to-Case		R _{thJC}	0.78	1.0		

Notes

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. $t \le 10 \text{ s.}$



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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Test Conditions Min.		Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	80			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3	V 	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	V		± 100	nA	
		$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 64 V, V _{GS} = 0 V, T _J = 125 °C			10	μA	
		V _{DS} = 64V, V _{GS} = 0 V, T _J = 175 °C			150		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 10 V, V _{GS} = 10 V	120			Α	
	D.	$V_{GS} = 10 \text{ V}, I_D = 30 \text{A}$		0.0039	0.0047	0	
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 20 A		0.0062	0.0077	Ω	
Forward Transconductance ^b	9 _{fs}	V _{DS} = 64 V, I _D = 30 A		78		S	
Dynamic	,						
Input Capacitance	C _{iss}			8865		pF	
Output Capacitance	Coss	$V_{GS} = 0 \text{ V}, V_{DS} = 40 \text{ V}, f = 1 \text{ MHz}$		2047			
Reverse Transfer Capacitance	C _{rss}			369			
Total Gate Charge ^c	Q_g			83	125		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 40 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 20 \text{A}$	25			nC	
Gate-Drain Charge ^c	Q _{gd}			30			
Turn-On Delay Time ^c	t _{d(on)}			12			
Rise Time ^c	t _r	$V_{DD} = 40 \text{ V}, R_{L} = 0.6 \Omega$		21			
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 30 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		53		ns	
Fall Time ^c	t _f			25			
Source-Drain Diode Ratings and Characteristics (T _C = 25 °C)							
Pulsed Current	I _{SM}				480	Α	
Diode Forward Voltage	V _{SD}	I _F = 20 A, V _{GS} = 0 V		0.8	1.5	V	
Reverse Recovery Time	t _{rr}	$I_F = 30 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		127		ns	
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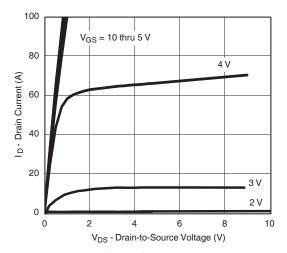
Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

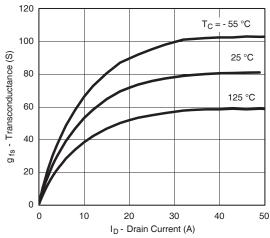
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



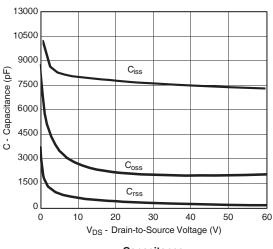
TYPICAL CHARACTERISTICS (25 °C unless noted)



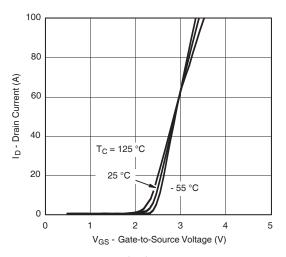
Output Characteristics



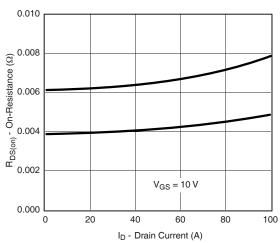
Transconductance



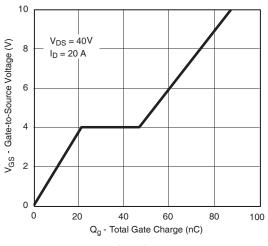
Capacitance



Transfer Characteristics



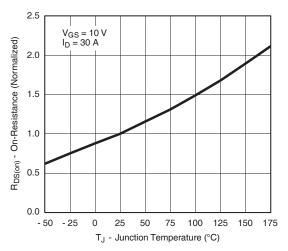
On-Resistance vs. Drain Current



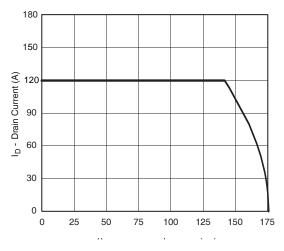
Gate Charge



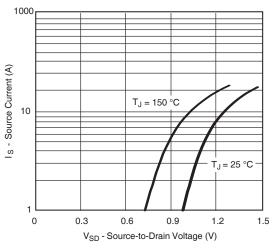
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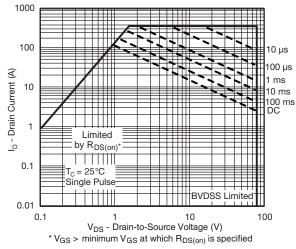
On-Resistance vs. Junction Temperature



Maximum Drain Current vs. Ambient Temperature



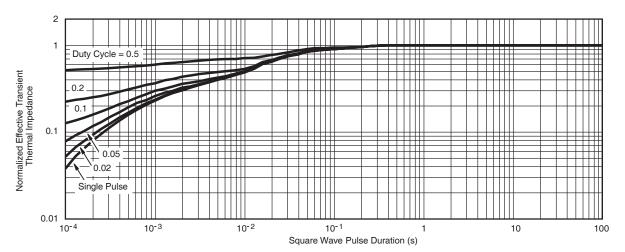
Source-Drain Diode Forward Voltage



Safe Operating Area



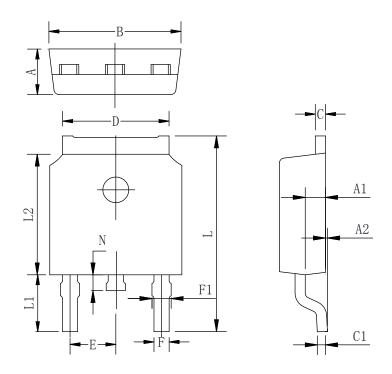
THERMAL RATINGS



Normalized Thermal Transient Impedance, Junction-to-Case



TO-252-2L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max		
A	2.10	2.30	2.50		
A1	0.88	1.01	1.16		
A2	0.00	0.15	0.28		
В	6.40	6.60	6.80		
С	0.42	0.50	0.63		
C1	0.42	0.50	0.63		
D	5.08	5.32	5.65		
Е	2.286 TYP				
F	0.63	0.76	0.89		
F1	0.64	0.86	1.08		
L	9.30	9.90	10.80		
L1	2.4	2.8	3.6		
L2	5.90	6.10	6.55		
N	0.57	0.80	1.05		

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